

Title (en)

METHOD FOR PRODUCING SCHOTTKY DIODES

Title (de)

VERFAHREN ZUR HERSTELLUNG VON SCHOTTKY-DIODEN

Title (fr)

PROCEDE DE PRODUCTION DE DIODES SCHOTTKY

Publication

EP 1145298 A2 20011017 (DE)

Application

EP 99934481 A 19990511

Priority

- DE 9901429 W 19990511
- DE 19823482 A 19980526

Abstract (en)

[origin: WO9962113A2] The invention relates to a method for producing Schottky diodes which comprise a guard ring (10) in the marginal area of the Schottky contact. Said guard ring (10) is produced by depositing a guard ring material (4) on the surface (8) of the semiconductor layer (2), said surface being provided with a structured masking layer (3) beforehand, and afterwards by siliconizing the guard ring material (4). The guard ring material (4) is a metal, especially a high barrier metal which, in particular, contains platinum.

IPC 1-7

H01L 21/329

IPC 8 full level

H01L 29/47 (2006.01); **H01L 21/329** (2006.01); **H01L 29/872** (2006.01)

CPC (source: EP US)

H01L 29/66143 (2013.01 - EP US); **H01L 29/872** (2013.01 - EP US)

Designated contracting state (EPC)

DE FI FR GB IT NL

DOCDB simple family (publication)

WO 9962113 A2 19991202; **WO 9962113 A3 20021003**; EP 1145298 A2 20011017; EP 1145298 A3 20021120; JP 2003514371 A 20030415; US 6551911 B1 20030422

DOCDB simple family (application)

DE 9901429 W 19990511; EP 99934481 A 19990511; JP 2000551431 A 19990511; US 49176700 A 20000126